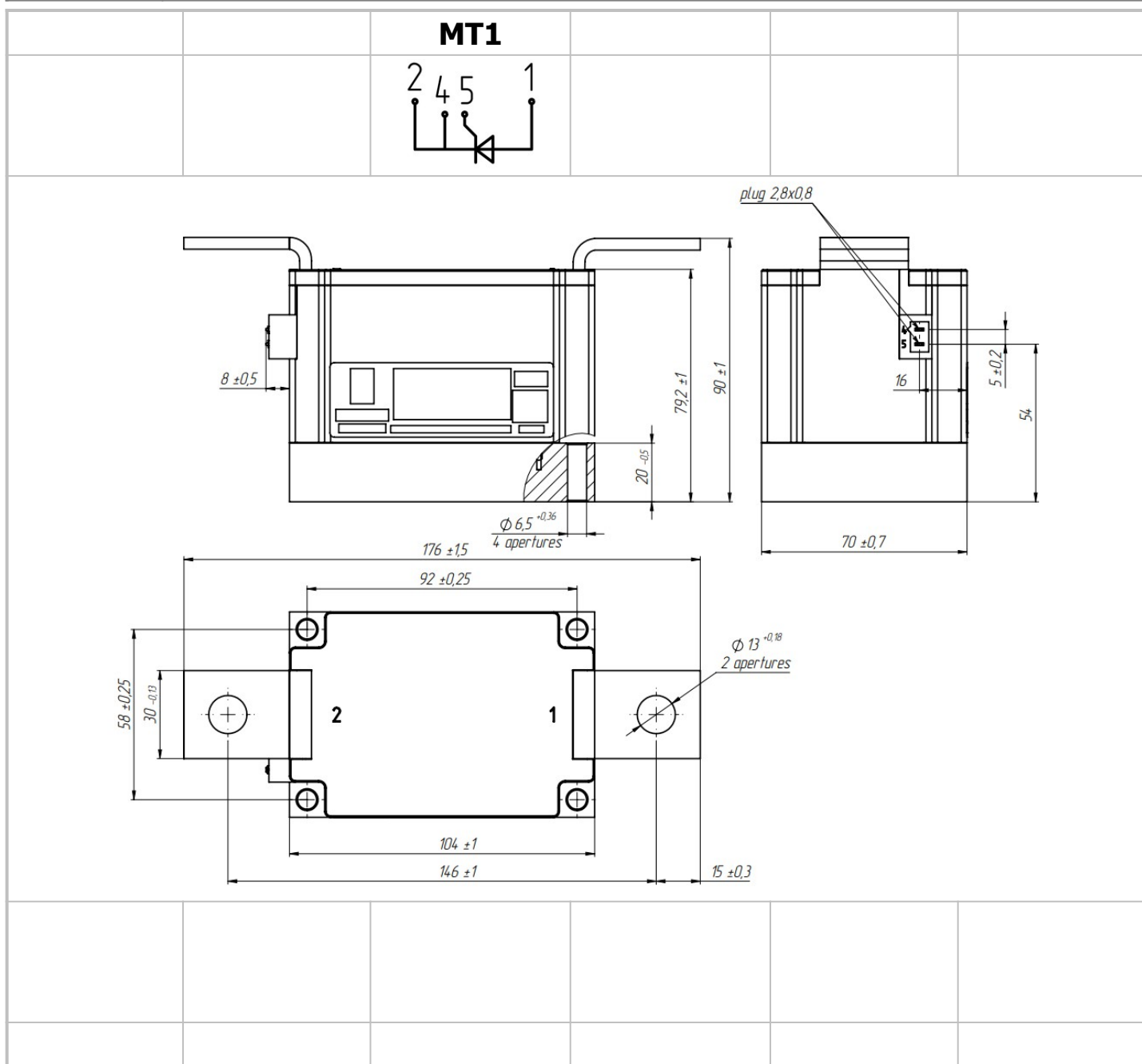




Electrically isolated base plate
Industrial standard package
Simplified mechanical design, rapid assembly
Pressure contact

Single Thyristor Module
For Phase Control
MT1-765-24-E1M

Maximum allowable mean on-state current		I _{TAV}	765 A
Repetitive peak off-state voltage		V _{DRM}	2000...2400 V
Repetitive peak reverse voltage		V _{RRM}	
Turn-off time		t _q	320 μs
V _{DRM} , V _{RRM} , V	2000	2200	2400
Voltage code	20	22	24
T _{ij} , °C	-50...+125		



MAXIMUM ALLOWABLE RATINGS

Symbols and parameters		Units	Values	Test conditions	
ON-STATE					
I_{TAV}	Maximum allowable mean on-state current	A	765 782	$T_c=86\text{ }^{\circ}\text{C}$; $T_c=85\text{ }^{\circ}\text{C}$; 180° half-sine wave; 50 Hz	
I_{TRMS}	RMS on-state current	A	1201	$T_c=86\text{ }^{\circ}\text{C}$; 180° half-sine wave; 50 Hz	
I_{TSM}	Surge on-state current	kA	35.5 41.0	$T_j=T_{j\max}$ $T_j=25\text{ }^{\circ}\text{C}$	180° half-sine wave; $t_p=10\text{ ms}$; single pulse; $V_D=V_R=0\text{ V}$; Gate pulse: $I_G=2\text{ A}$; $V_G=20\text{ V}$; $t_{GP}=500\text{ }\mu\text{s}$; $di_G/dt=1\text{ A}/\mu\text{s}$
			37.0 43.0	$T_j=T_{j\max}$ $T_j=25\text{ }^{\circ}\text{C}$	180° half-sine wave; $t_p=8.3\text{ ms}$; single pulse; $V_D=V_R=0\text{ V}$; Gate pulse: $I_G=2\text{ A}$; $V_G=20\text{ V}$; $t_{GP}=500\text{ }\mu\text{s}$; $di_G/dt=1\text{ A}/\mu\text{s}$
I^2t	Safety factor	$\text{A}^2\text{s}\cdot 10^3$	6300 8400	$T_j=T_{j\max}$ $T_j=25\text{ }^{\circ}\text{C}$	180° half-sine wave; $t_p=10\text{ ms}$; single pulse; $V_D=V_R=0\text{ V}$; Gate pulse: $I_G=2\text{ A}$; $V_G=20\text{ V}$; $t_{GP}=500\text{ }\mu\text{s}$; $di_G/dt=1\text{ A}/\mu\text{s}$
			5600 7600	$T_j=T_{j\max}$ $T_j=25\text{ }^{\circ}\text{C}$	180° half-sine wave; $t_p=8.3\text{ ms}$; single pulse; $V_D=V_R=0\text{ V}$; Gate pulse: $I_G=2\text{ A}$; $V_G=20\text{ V}$; $t_{GP}=500\text{ }\mu\text{s}$; $di_G/dt=1\text{ A}/\mu\text{s}$
BLOCKING					
V_{DRM}, V_{RRM}	Repetitive peak off-state and Repetitive peak reverse voltages	V	2000...2400	$T_{j\min} < T_j < T_{j\max}$; 180° half-sine wave; 50 Hz; Gate open	
V_{DSM}, V_{RSM}	Non-repetitive peak off-state and Non-repetitive peak reverse voltages	V	2100...2500	$T_{j\min} < T_j < T_{j\max}$; 180° half-sine wave; single pulse; Gate open	
V_D, V_R	Direct off-state and Direct reverse voltages	V	$0.6\cdot V_{DRM}$ $0.6\cdot V_{RRM}$	$T_j=T_{j\max}$; Gate open	
TRIGGERING					
I_{FGM}	Peak forward gate current	A	8	$T_j=T_{j\max}$	
V_{RGM}	Peak reverse gate voltage	V	5		
P_G	Gate power dissipation	W	4	$T_j=T_{j\max}$ for DC gate current	
SWITCHING					
$(di_T/dt)_{crit}$	Critical rate of rise of on-state current non-repetitive (f=1 Hz)	A/ μs	1250	$T_j=T_{j\max}$; $V_D=0.67\cdot V_{DRM}$; $I_{TM}=1500\text{ A}$; Gate pulse: $I_G=2\text{ A}$; $V_G=20\text{ V}$; $t_{GP}=50\text{ }\mu\text{s}$; $di_G/dt=2\text{ A}/\mu\text{s}$	
THERMAL					
T_{stg}	Storage temperature	$^{\circ}\text{C}$	-50...+50		
T_j	Operating junction temperature	$^{\circ}\text{C}$	-50...+125		
$T_{c\text{ op}}$	Operating temperature	$^{\circ}\text{C}$	-50...+125		
MECHANICAL					
a	Acceleration under vibration	m/s ²	50		

CHARACTERISTICS

Symbols and parameters		Units	Values	Conditions	
ON-STATE					
V _{TM}	Peak on-state voltage, max	V	1.50	T _j =25 °C; I _{TM} =2500 A	
V _{T(TO)}	On-state threshold voltage, max	V	0.865	T _j =T _{j max} ;	
r _T	On-state slope resistance, max	mΩ	0.215	0.5 π I _{TAV} < I _T < 1.5 π I _{TAV}	
I _L	Latching current, max	mA	1500	T _j =25 °C; V _D =12 V; Gate pulse: I _G =I _{FGM} ; V _G =20 V; t _{GP} =500 μs; di _G /dt=1 A/μs	
I _H	Holding current, max	mA	300	T _j =25 °C; V _D =12 V; Gate open	
BLOCKING					
I _{DRM} , I _{RRM}	Repetitive peak off-state and Repetitive peak reverse currents, max	mA	150 4.00	T _j =T _{j max} T _j = 25 °C	V _D =V _{DRM} ; V _R =V _{RRM}
(dv _D /dt) _{crit}	Critical rate of rise of off-state voltage ¹⁾ , min	V/μs	200, 320, 500, 1000, 1600, 2000, 2500	T _j =T _{j max} ; V _D =0.67·V _{DRM} ; Gate open	
TRIGGERING					
V _{GT}	Gate trigger direct voltage, max	V	3.00 2.50 1.50	T _j = T _{j min} T _j =25 °C T _j = T _{j max}	V _D =12 V; I _D =3 A; Direct gate current
I _{GT}	Gate trigger direct current, max	mA	400 250 150	T _j = T _{j min} T _j = 25 °C T _j = T _{j max}	
V _{GD}	Gate non-trigger direct voltage, min	V	0.50	T _j =T _{j max} ; V _D =0.67·V _{DRM} ;	
I _{GD}	Gate non-trigger direct current, min	mA	65.00	Direct gate current	
SWITCHING					
t _{gd}	Delay time, max	μs	1.10	T _j =25 °C; V _D =1000 V; I _{TM} =I _{TAV} ; di/dt=200 A/μs;	
t _{gt}	Turn-on time, max	μs	3.00	Gate pulse: I _G =2 A; V _G =20 V; t _{GP} =50 μs; di _G /dt=2 A/μs	
t _q	Turn-off time ²⁾ , max	μs	320	dv _D /dt=50 V/μs; T _j =T _{j max} ; I _{TM} =I _{TAV} ; di _R /dt=-10 A/μs; V _R =100 V; V _D =0.67·V _{DRM}	
Q _{rr}	Recovered charge, max	μC	3480	T _j =T _{j max} ; I _{TM} =I _{TAV} ;	
t _{rr}	Reverse recovery time, max	μs	40	di _R /dt=-10 A/μs;	
I _{rr}	Reverse recovery current, max	A	174	V _R =100 V	
THERMAL					
R _{thjc}	Thermal resistance, junction to case			180° half-sine wave, 50 Hz	
	per module	°C/W	0.0400		
R _{thch}	Thermal resistance, case to heatsink				
	per module	°C/W	0.0100		
INSULATION					
V _{ISOL}	Insulation test voltage	kV	4.50	Sine wave, 50 Hz; RMS	t=60 sec
			5.40		t=1 sec
MECHANICAL					
M ₁	Mounting torque (M6) ³⁾	Nm	6.00	Tolerance ± 15%	
M ₂	Terminal connection torque (M12) ³⁾	Nm	18.00	Tolerance ± 15%	
m	Weight, max	g	2750		

PART NUMBERING GUIDE													NOTES																					
MT	1	-	765	-	24	-	A2	K2	-	E1M	-	N																						
1	2		3		4		5	6		7		8																						
1. MT - Thyristor module														1) Critical rate of rise of off-state voltage <table><tr><td>Symbol of Group</td><td>P2</td><td>K2</td><td>E2</td><td>A2</td><td>T1</td><td>P1</td><td>M1</td></tr><tr><td>(dv_D/dt)_{crit}, V/μs</td><td>200</td><td>320</td><td>500</td><td>1000</td><td>1600</td><td>2000</td><td>2500</td></tr></table> 2) Turn-off time (dv_D/dt=50 V/μs) <table><tr><td>Symbol of Group</td><td>K2</td></tr><tr><td>t_{qr}, μs</td><td>320</td></tr></table> 3) The screws must be lubricated 4) Additionally: - ambient operating temperature −50...+60 °C; - maximum altitude above sea level 1700 meters; - frost and dew resistance.	Symbol of Group	P2	K2	E2	A2	T1	P1	M1	(dv _D /dt) _{crit} , V/μs	200	320	500	1000	1600	2000	2500	Symbol of Group	K2	t _{qr} , μs	320
Symbol of Group	P2	K2	E2	A2	T1	P1	M1																											
(dv _D /dt) _{crit} , V/μs	200	320	500	1000	1600	2000	2500																											
Symbol of Group	K2																																	
t _{qr} , μs	320																																	
2. Circuit Schematic																																		
3. Average On-state Current, A																																		
4. Voltage Code																																		
5. Critical rate of rise of off-state voltage																																		
6. Group of turn-off time (dv _D /dt=50 V/μs)																																		
7. Package Type (M.E1M)																																		
8. Ambient Conditions: N – Normal ⁴⁾																																		

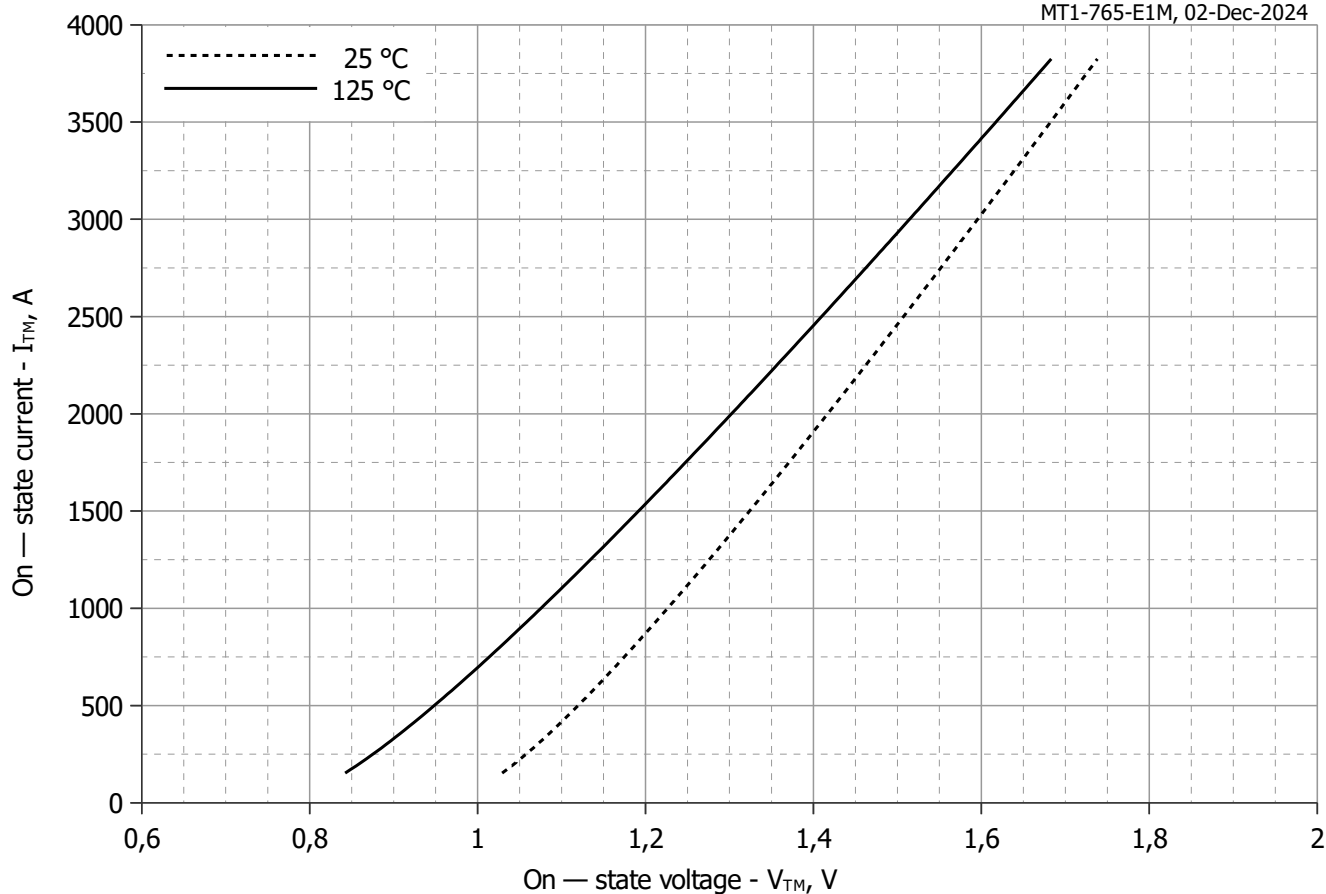


Fig 1 – On-state characteristics of Limit device

Analytical function for On-state characteristic:

$$V_T = A + B \cdot i_T + C \cdot \ln(i_T + 1) + D \cdot \sqrt{i_T}$$

	Coefficients for max curves	
	$T_j = 25^\circ\text{C}$	$T_j = T_{j\max}$
A	0.93355545	0.75300536
B	0.00014227	0.00016275
C	0.00643563	0.00085979
D	0.00335204	0.00486089

On-state characteristic model (see Fig. 1)

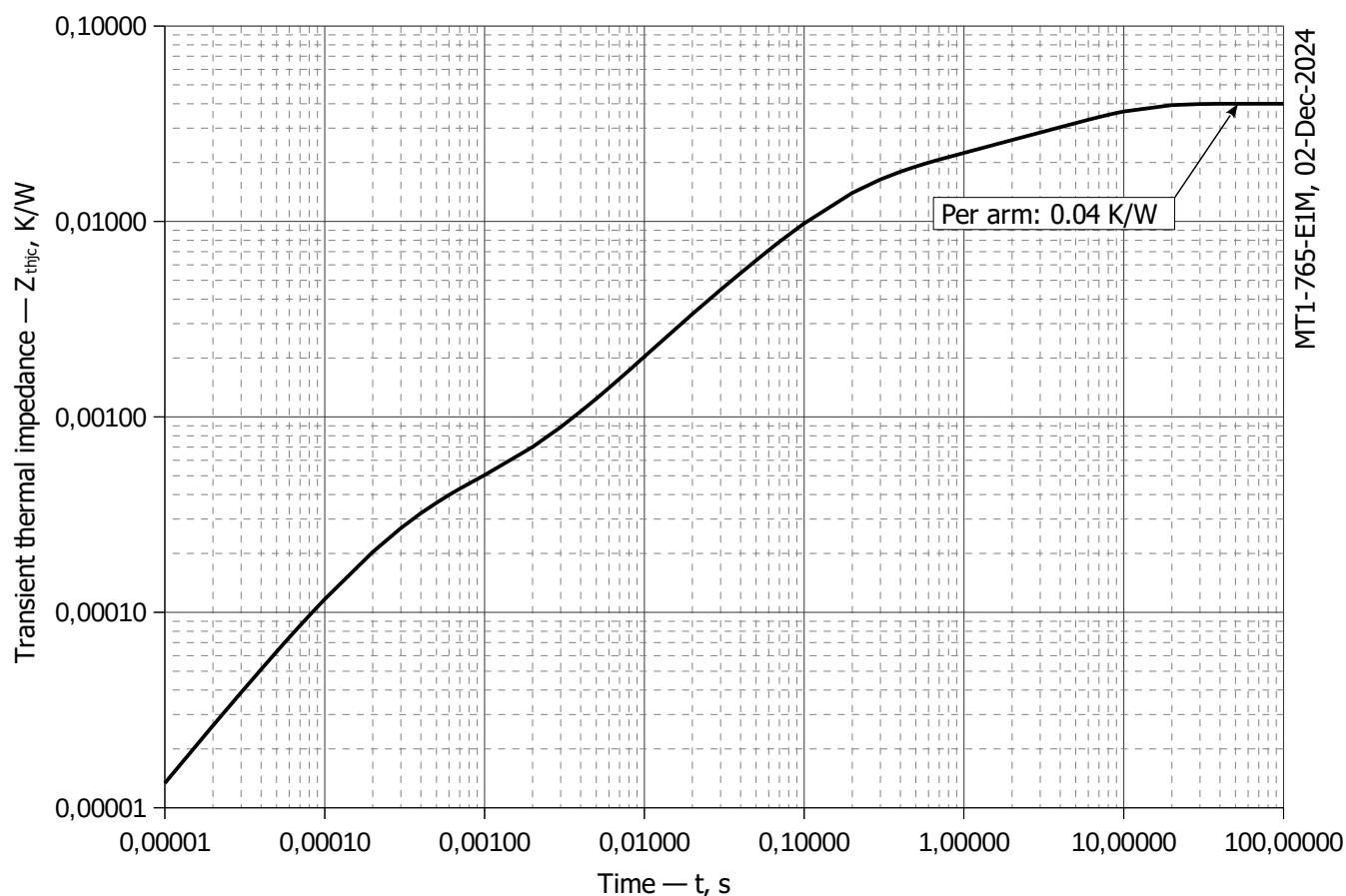


Fig 2 – Transient thermal impedance Z_{thjc} vs. time t

Analytical function for Transient thermal impedance junction to case Z_{thjc} for DC:

$$Z_{thjc} = \sum_{i=1}^n R_i \left(1 - e^{-\frac{t}{\tau_i}} \right)$$

Where $i = 1$ to n , n is the number of terms in the series.

t = Duration of heating pulse in seconds.

Z_{thjc} = Thermal resistance at time t .

R_i = Amplitude of p_{th} term.

τ_i = Time constant of r_{th} term.

i	1	2	3	4	5	6
R_i , K/W	0.0189958	0.005931	0.009502	0.004252	0.001006	0.0003132
τ_i , s	5.887	0.7389	0.1616	0.08215	0.01267	0.0002712

Transient thermal impedance junction to case Z_{thjc} model (see Fig. 2)

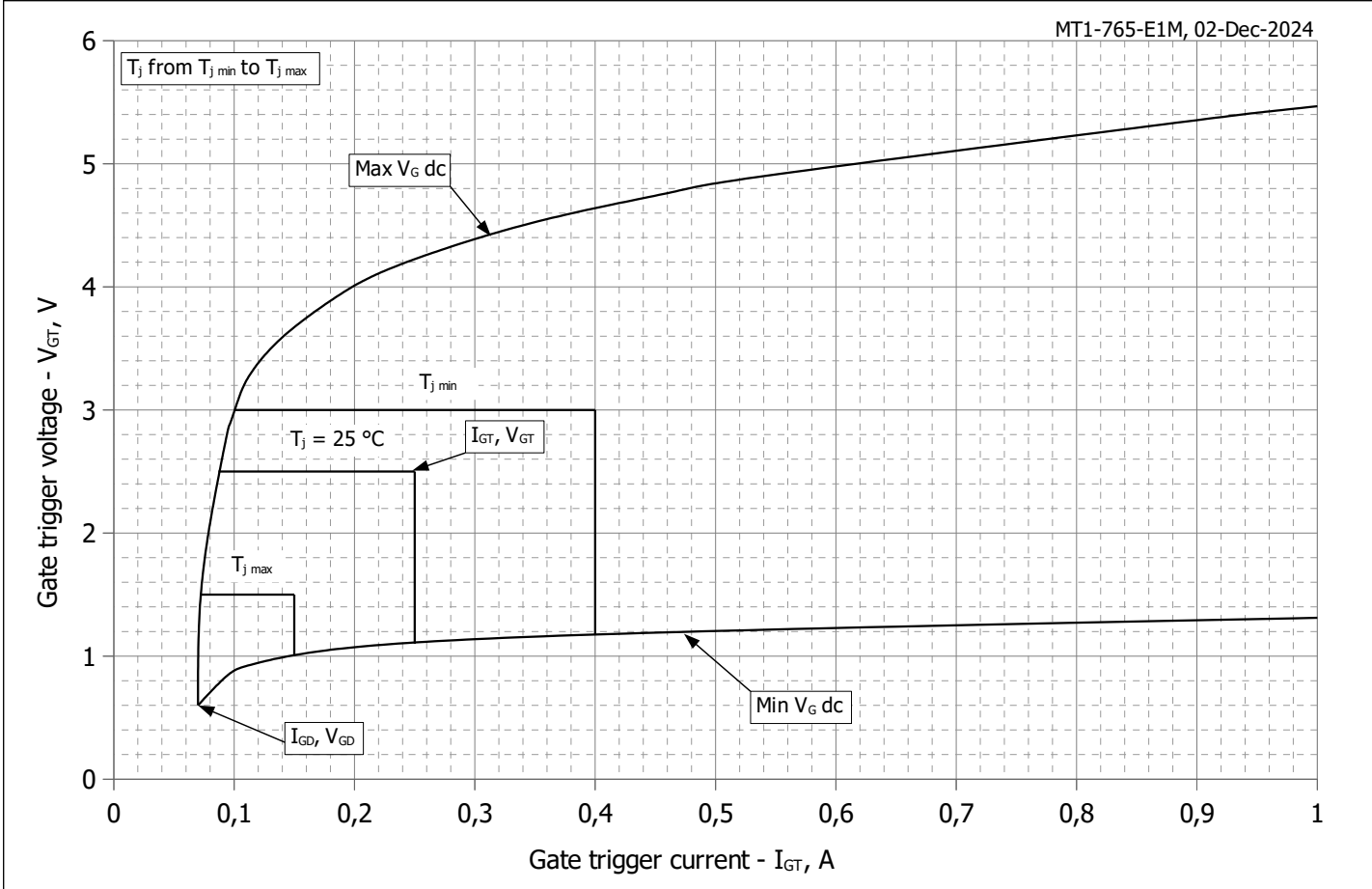


Fig 3 – Gate characteristics – Trigger limits

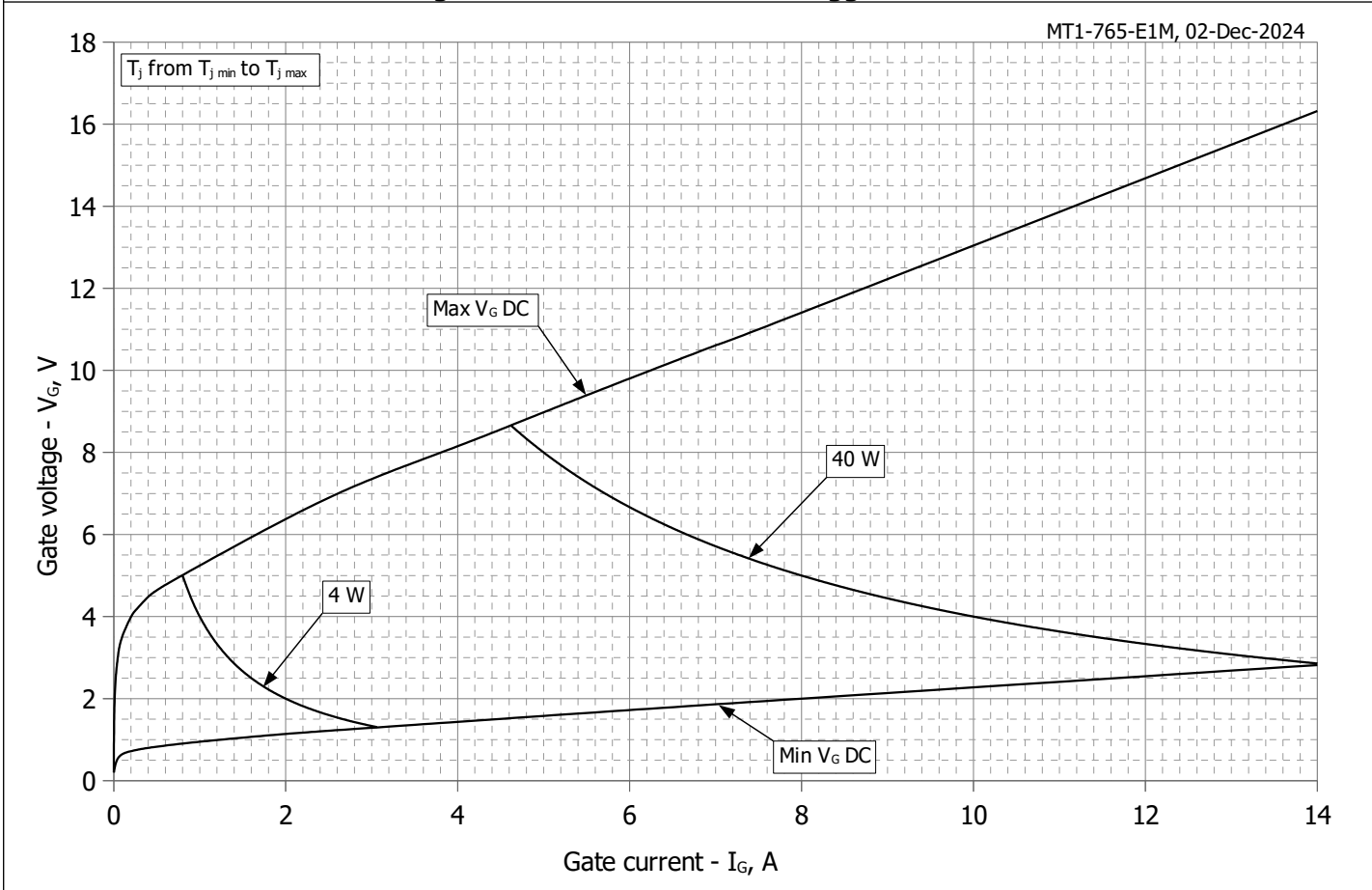


Fig 4 - Gate characteristics –Power curves

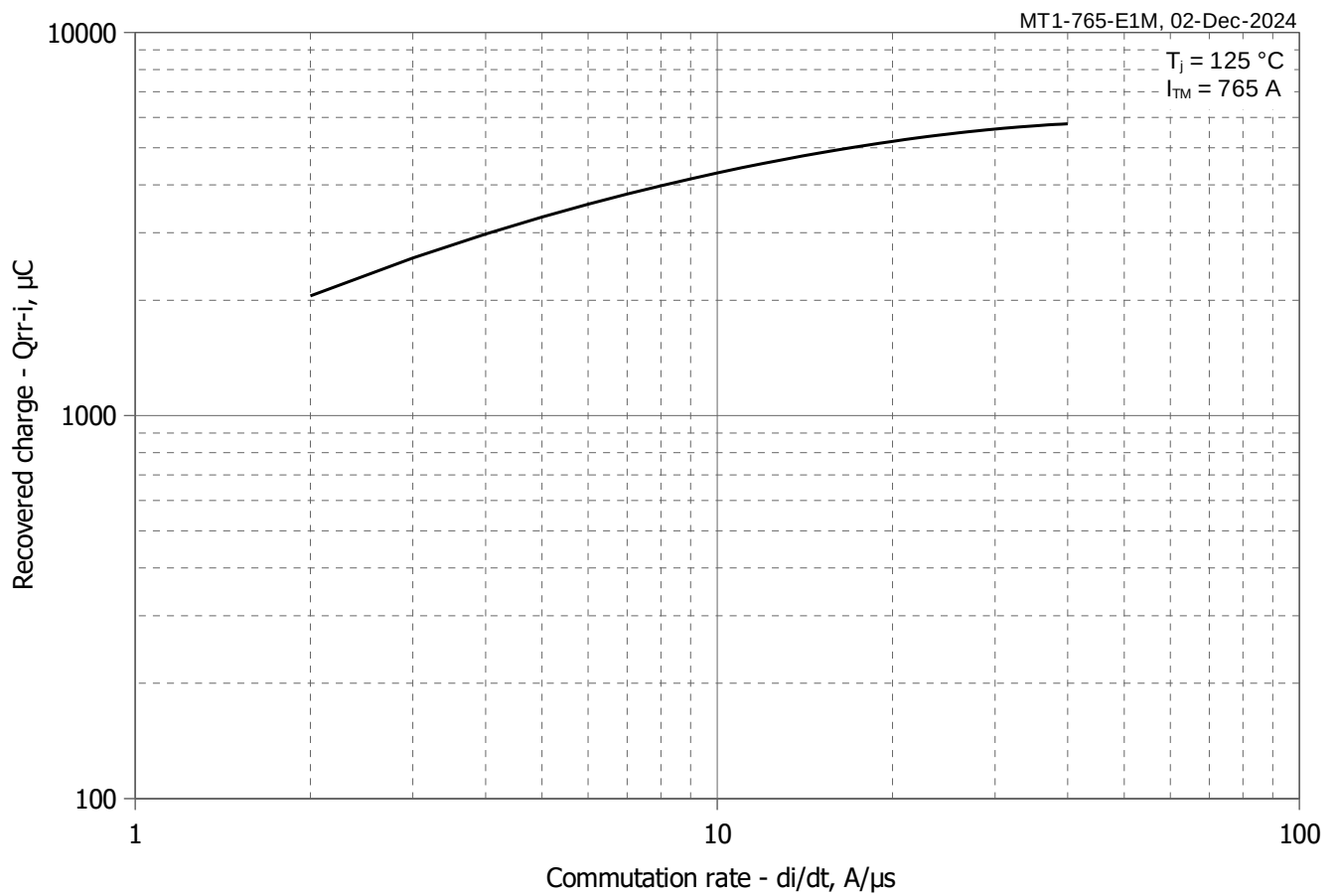


Fig 5 – Maximum recovered charge Q_{rr-i} (integral) vs. commutation rate di_R/dt

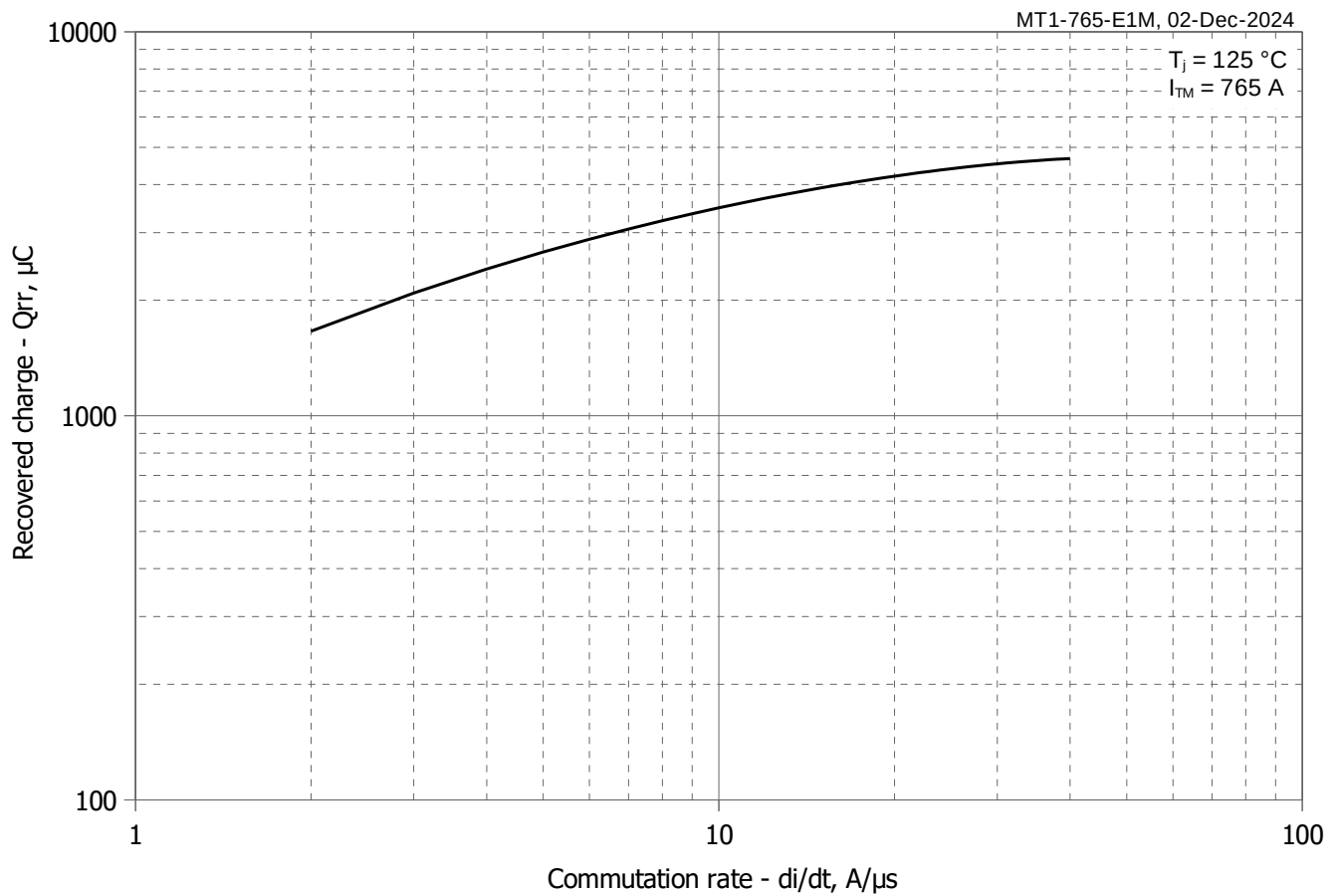


Fig 6 – Maximum recovered charge Q_{rr} vs. commutation rate di_R/dt (25% chord)

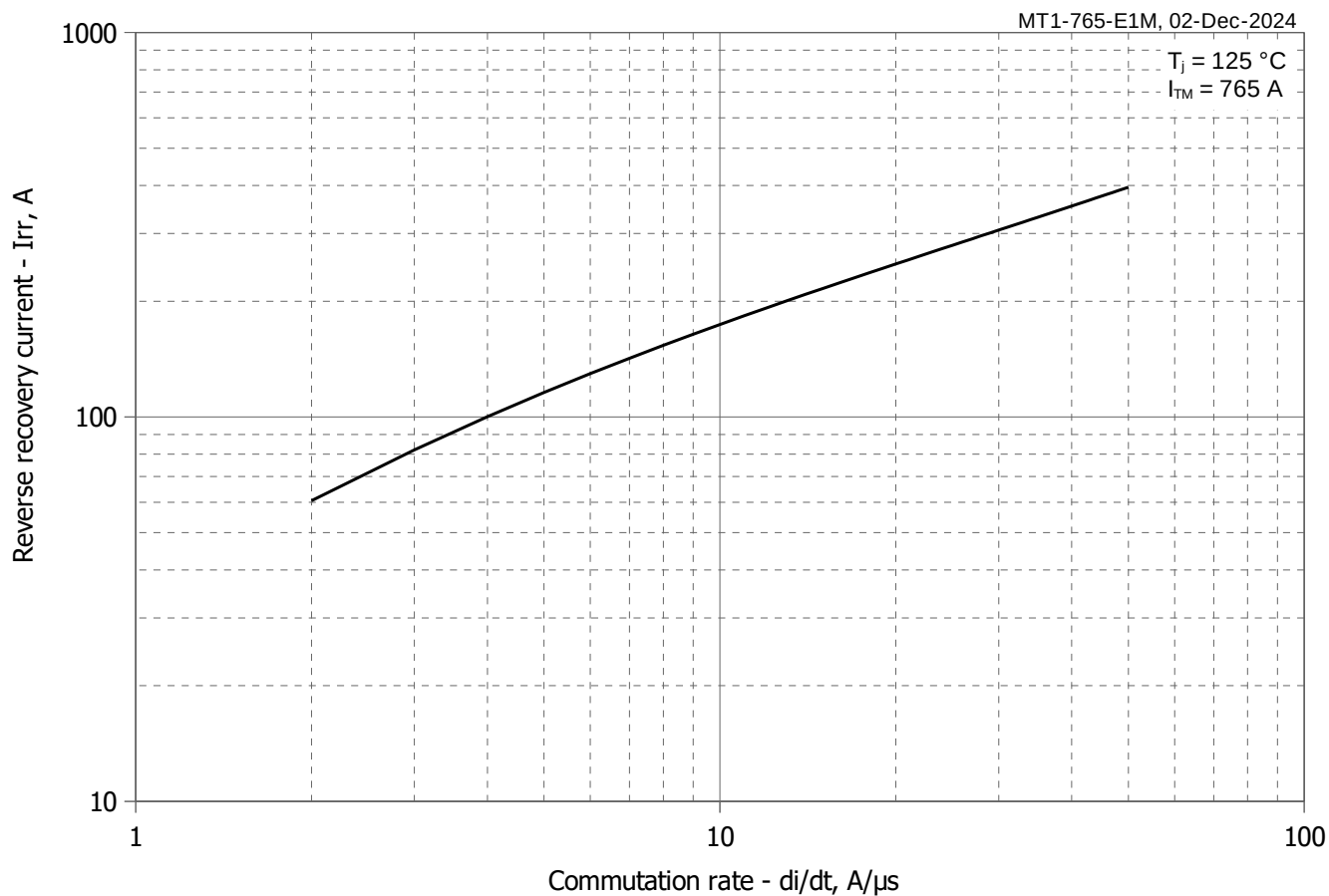


Fig 7 – Maximum reverse recovery current I_{rr} vs. commutation rate di_R/dt

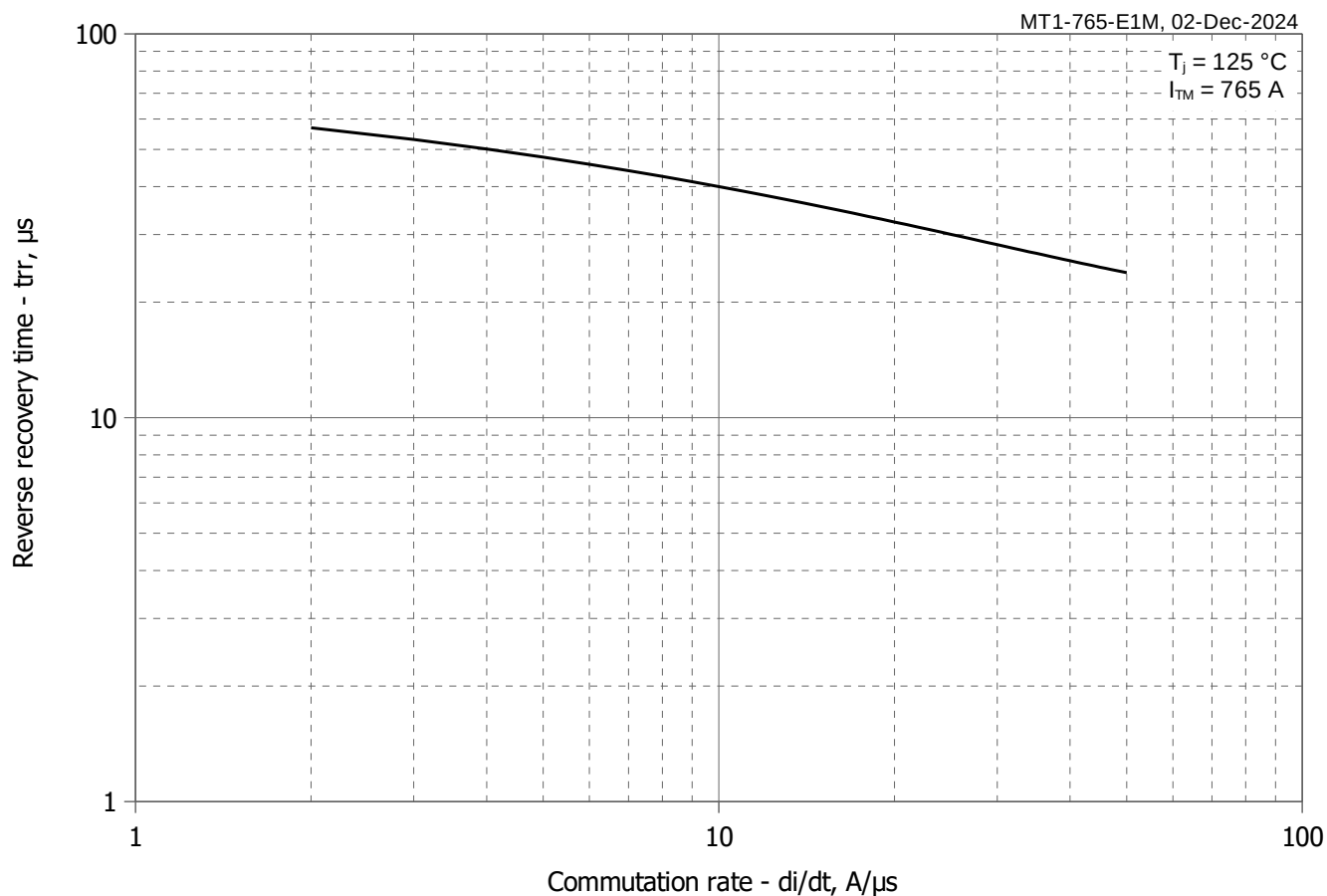


Fig 8 – Maximum recovery time t_r vs. commutation rate di_R/dt (25% chord)

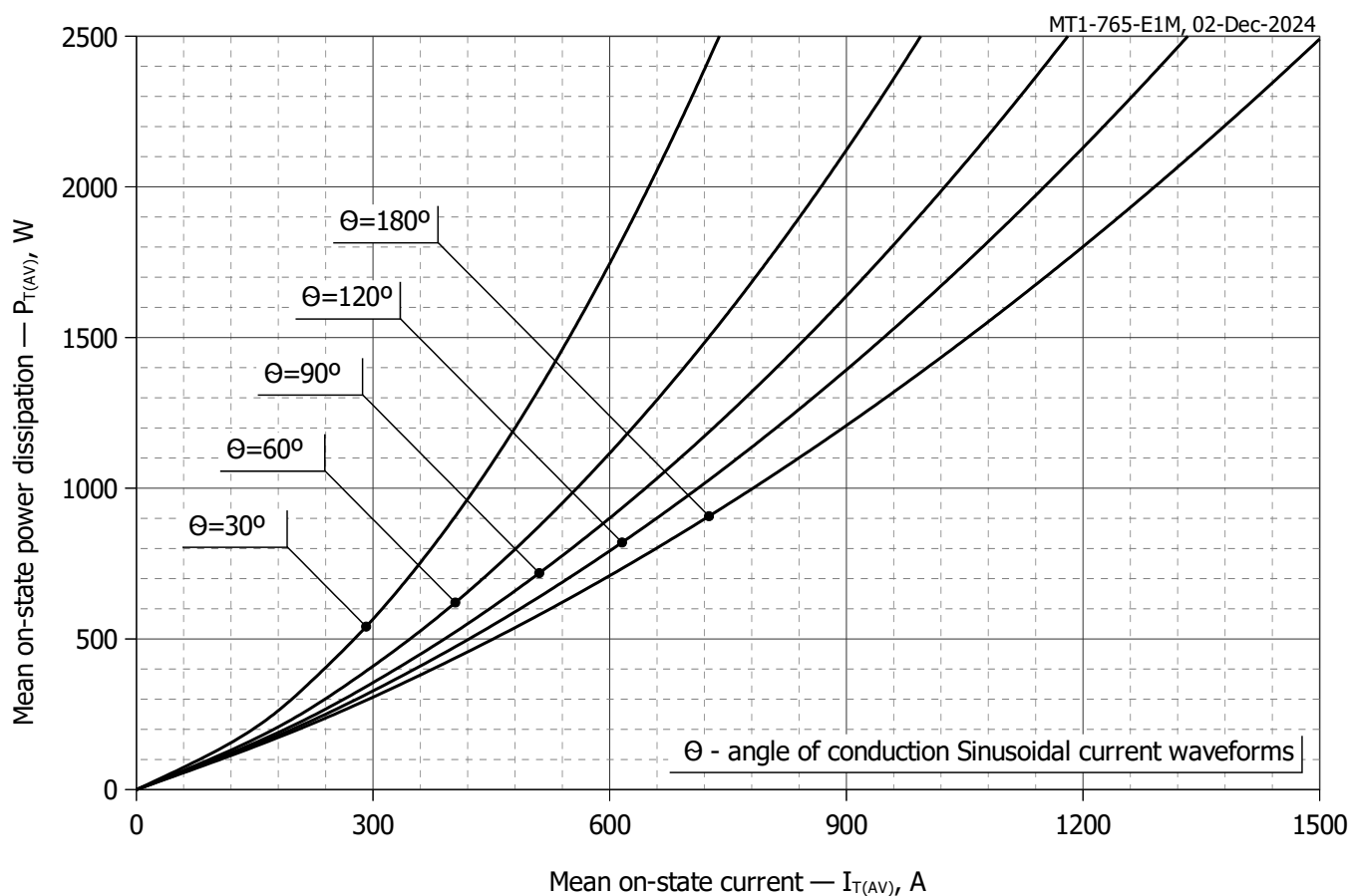


Fig. 9 - Mean on-state power dissipation P_{TAV} vs. mean on-state current I_{TAV} for sinusoidal current waveforms at different conduction angles ($f=50\text{Hz}$)

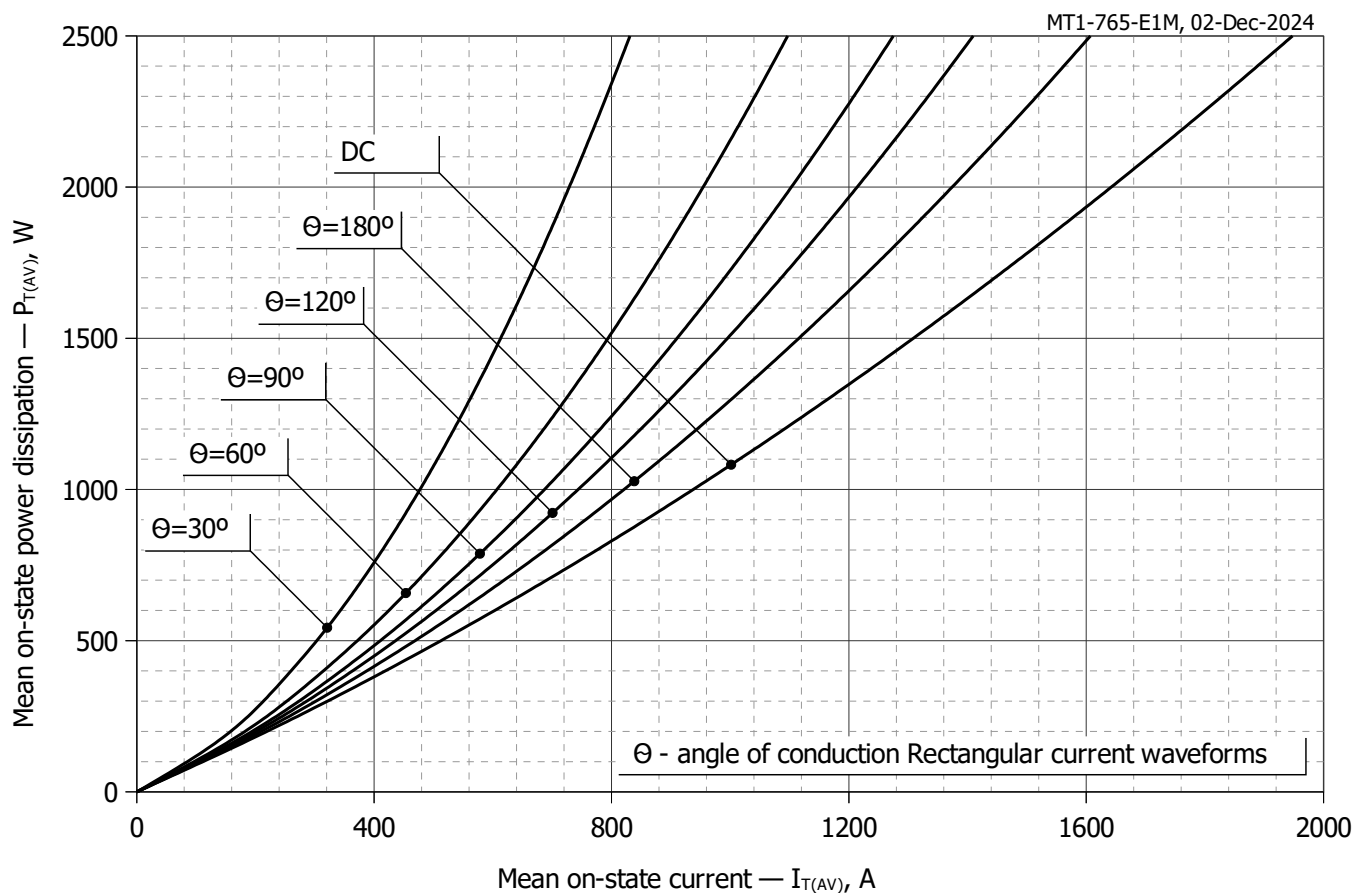


Fig. 10 – Mean on-state power dissipation P_{TAV} vs. mean on-state current I_{TAV} for rectangular current waveforms at different conduction angles and for DC ($f=50\text{Hz}$)

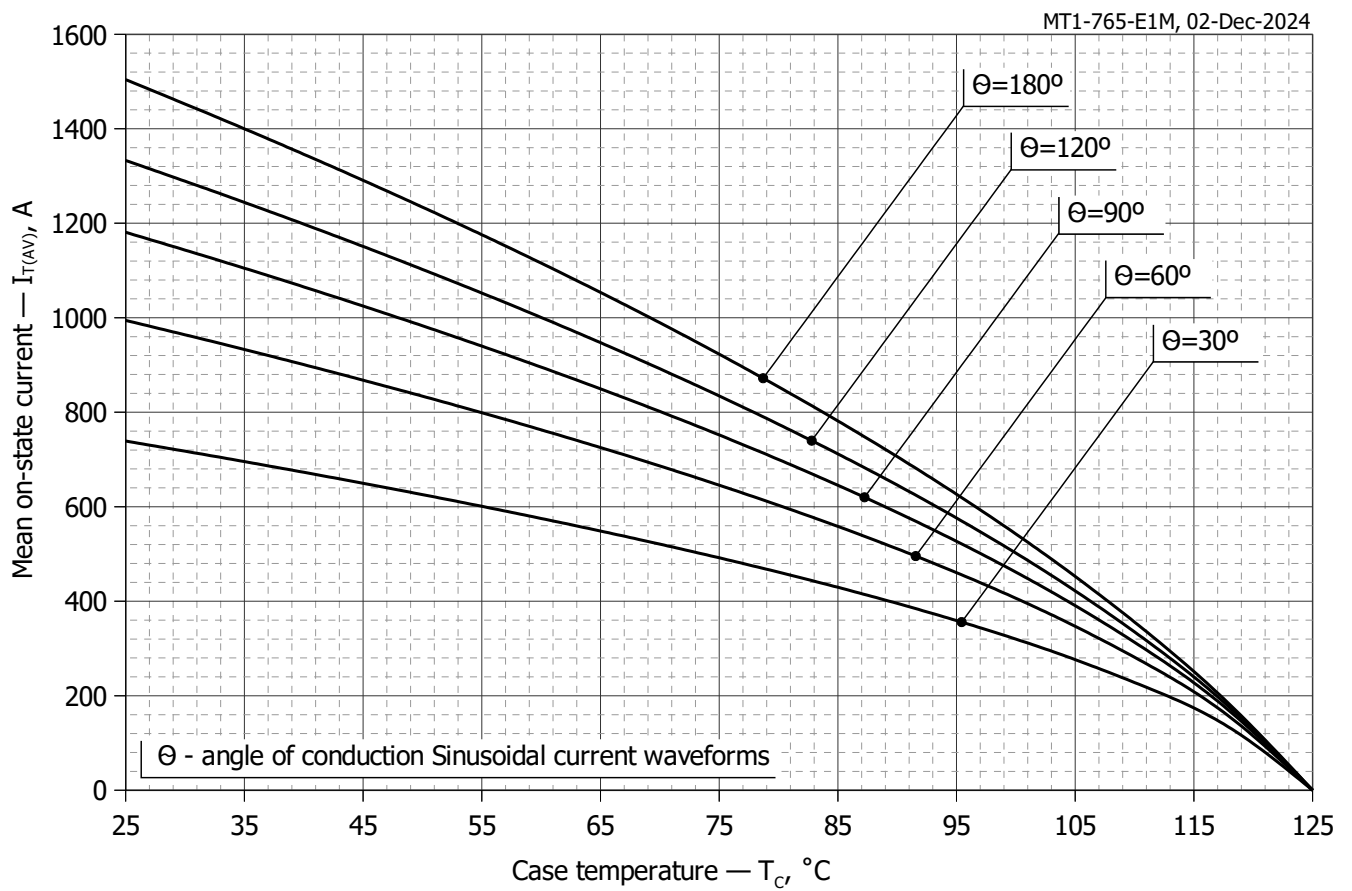


Fig. 11 – Mean on-state current I_{TAV} vs. case temperature T_C for sinusoidal current waveforms at different conduction angles ($f=50\text{Hz}$)

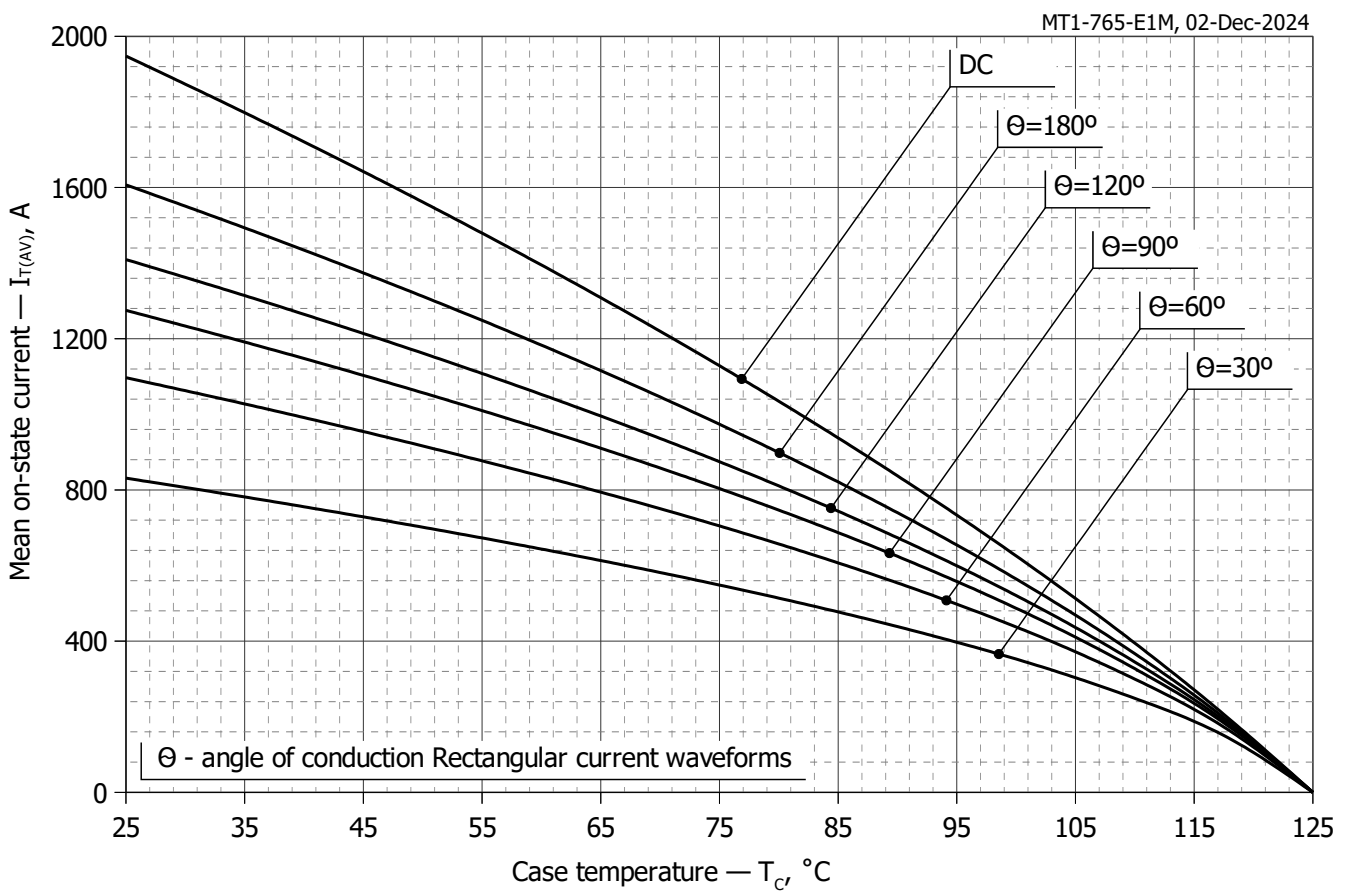


Fig. 12 - Mean on-state current I_{TAV} vs. case temperature T_C for rectangular current waveforms at different conduction angles and for DC ($f=50\text{Hz}$)

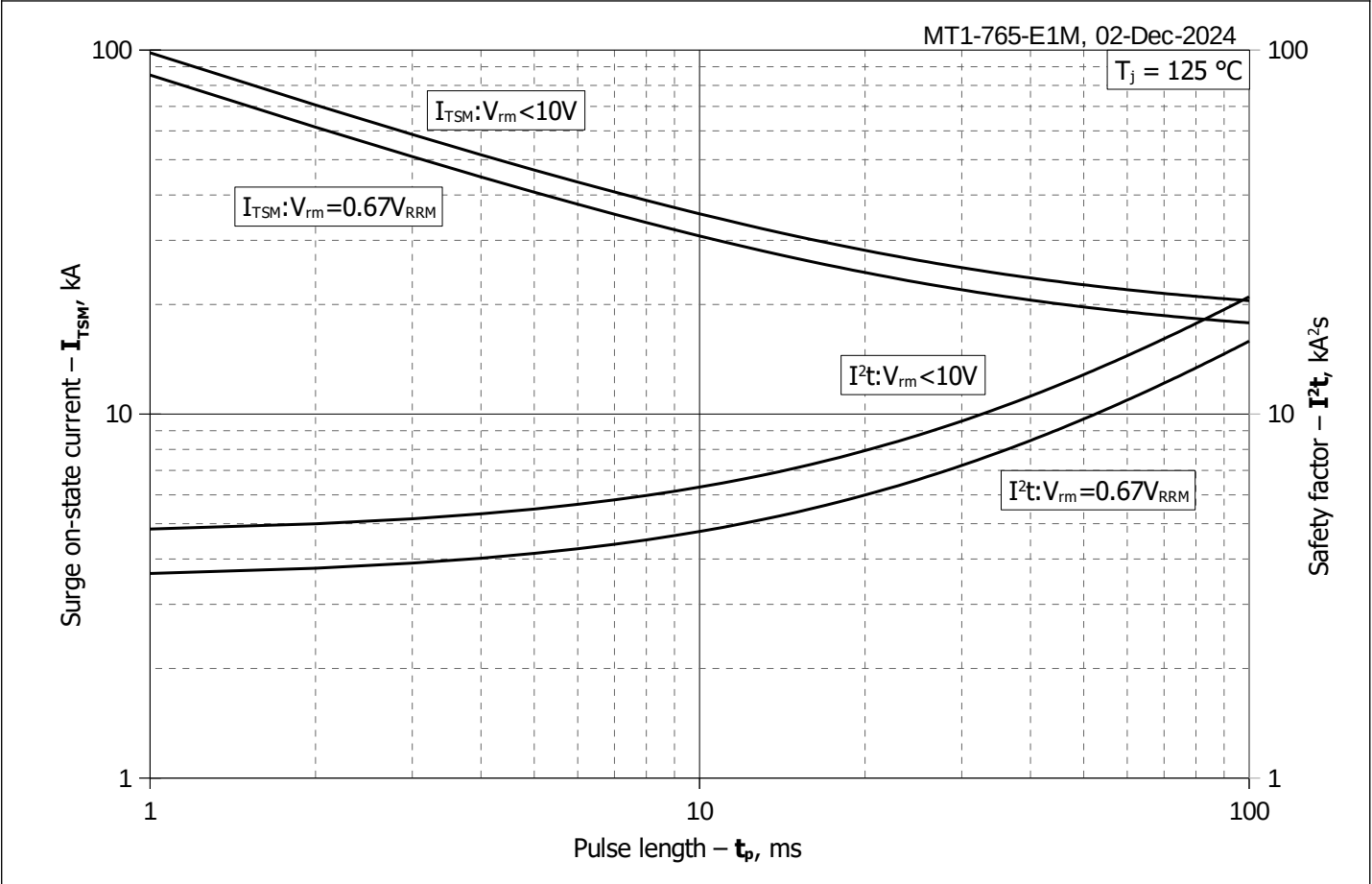


Fig. 13 – Maximum surge on-state current I_{TSM} and safety factor I^2t vs. pulse length t_p

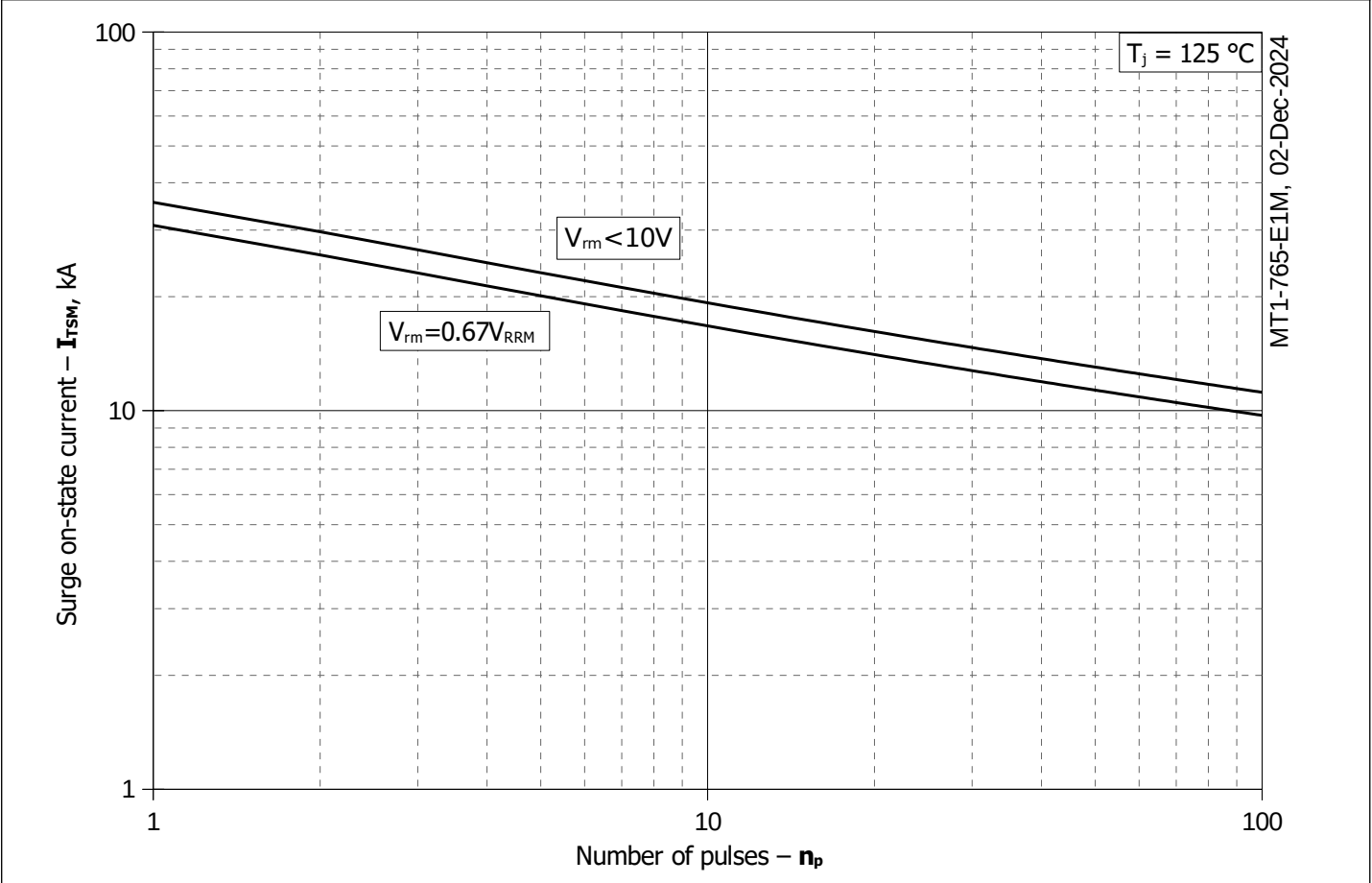


Fig. 14 - Maximum surge on-state current I_{TSM} vs. number of pulses n_p